



Polyfet is now manufacturing GaN (on SiC) devices. These devices offer the following advantages:

- Higher power density (4-6W/mm)
- Higher efficiencies (>70% at P3dB)
- GaN of SiC, which is thermally superior to GaN on Si
- Superior broad band response over D-MOS (usable gain up to 3GHz)
- +200Vdc drain break down voltages (operational across 24-60Vdc)
- Mounted in thermally enhanced packages
- Typically used in broad band communication, jamming, and instrumentation amplifiers

Devices available thus far:

Device	P3dB, 48Vdc (200-2000MHz)	P3dB, 48Vdc	Status
GP041	5W	10W @ 2.5GHz	
GP141	15W	35W @ 2.5GHz	
GX141	15W	35W @ 2.5GHz	
GX241	35W	60W @ 2GHz	Will characterize at 2.5GHz by 12/1/11
GX341	60W	85W @ 2GHz	Will characterize at 2.5GHz by 12/1/11
GX242	75W	120W @ 2GHz	

Polyfet has been shipping in volume High Power RF Mosfet Transistors employing both State of the Art LDMOS (Lateral) and VDMOS (Vertical) silicon gate technologies since 1988. In early 2010, the full line of GaN devices was released. Polyfet is located about an hour's drive North West of Los Angeles, California. A privately held company we have a proud history of providing excellence in service, delivering quality products on time and full technical support to assist customers' engineers in selecting and designing our transistors into their amplifiers. Polyfet's products have long life time cycles of over fifteen years making them suitable for Military applications. For those who use software to design amplifiers, a set of S parameters and Spice models can be downloaded from our web site.